

FMMT413

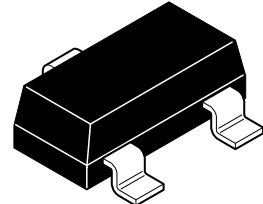
SOT23 NPN silicon planar avalanche transistor

Summary

$V_{(BR)CES} = 150V$, $V_{(BR)CEO} = 50V$, $I_{USB} = 25A$

Description

The FMMT413 is a NPN silicon planar bipolar transistor optimized for avalanche mode operation. Tight process control and low inductance packaging combine to produce high current pulses with fast edges, ideal for laser diode driving.

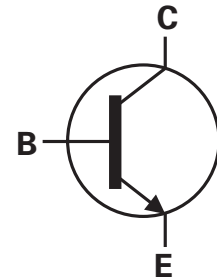


Features

- Avalanche mode operation
- 50A peak avalanche current
- Low inductance packaging

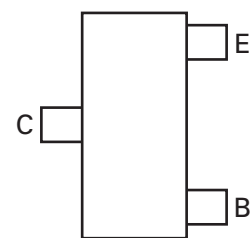
Applications

- Laser LED drivers
- Fast edge generation
- High speed pulse generators



Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT413TD	7	8	500
FMMT413TA	7	8	3,000



Pinout - top view

Device marking

413

FMMT413

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	BV_{CBO}	150	V
Collector-emitter voltage	BV_{CEO}	50	V
Emitter-base voltage	BV_{EBO}	6	V
Peak pulse current (25ns Pulse Width)	I_{CM}	50	A
Continuous collector current	I_C	100	mA
Power dissipation at $T_{amb} = 25^\circ\text{C}$ Linear derating factor	P_D	330	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient	$R_{\theta JA}$	378	$^\circ\text{C/W}$

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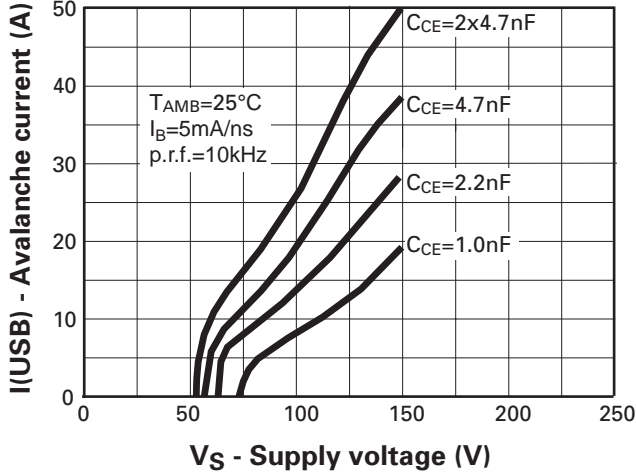
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	150			V	
Collector-emitter breakdown voltage	BV_{CES}	150			V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	50			V	$I_C = 10\text{mA}$
Emitter-base breakdown voltage	BV_{EBO}	6			V	$I_E = 100\mu\text{A}$
Collector cut-off current	I_{CBO}			100	nA	$V_{CB} = 120\text{V}$
Emitter cut-off current	I_{EBO}			100	nA	$V_{EB} = 4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$			150	mV	$I_C = 10\text{mA}$, $I_B = 1\text{mA}$
Base-emitter saturation voltage	$V_{BE(sat)}$			800	mV	$I_C = 10\text{mA}$, $I_B = 1\text{mA}$
Current in second breakdown (pulsed)	I_{USB}	22			A	$V_C = 110\text{V}$, $C_{CE} = 4.7\text{nF}^{(*)}$
		25			A	$V_C = 130\text{V}$, $C_{CE} = 4.7\text{nF}^{(*)}$
Static forward current transfer ratio	h_{FE}	50				$I_C = 10\text{mA}$, $V_{CE} = 10\text{V}$
Collector-emitter inductance	L_{ce}		2.5		nH	Standard SOT23 leads
Transition frequency	f_T		150		MHz	$I_C = 10\text{mA}$, $V_{CE} = 5\text{V}$, $f = 20\text{MHz}$
Output capacitance	C_{OBO}		2		pF	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$

NOTES:

(*) Measured with a circuit possessing an approximate loop inductance of 12nH.

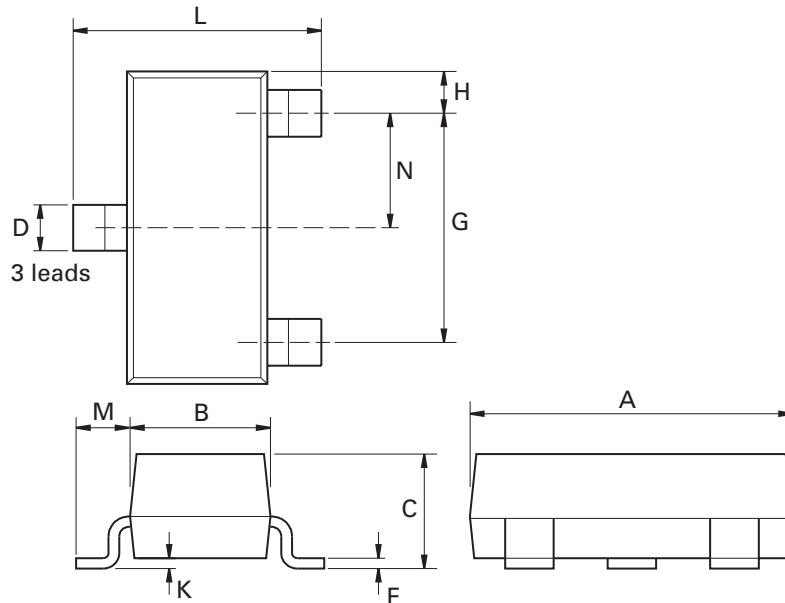
Typical characteristics



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FMMT413

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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